

Electronic Supplementary Information (ESI)

Photon energy transfer by quantum dots in the organic-inorganic hybrid solar cells through FRET

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Contents

Figure S1. Properties of InP QDs. Ultraviolet photoemission spectroscopy (UPS) to determine energy levels of InP QDs

Figure S2. Performance optimization of BHJ + QDs hybrid solar cells : Current-density versus voltage (J-V) characteristics of conventional InP QDs + PC₇₁BM BHJ solar cells under AM 1.5 G illumination with an irradiation intensity of 93 mW cm⁻²

Figure S3. Electrostatic force microscopy (EFM) characteristics of (a) BHJ active layer, (b) BHJ + QDs hybrid active layer, (c) BHJ active layer with PFN interlayer and (d) BHJ + QDs hybrid active layer with PFN interlayer.

Figure S4. Dark current characteristics of BHJ + InP QDs hybrid solar cells under AM 1.5 G illumination with an irradiation intensity of 93 mW cm⁻²

Figure S5. Ratio optimization of BHJ + QDs hybrid solar cells : Current density versus voltage (J-V) characteristics of conventional InP Qs + PC₇₁BM solar cells under AM 1.5 G illumination with an irradiation intensity of 93 mW cm⁻²

Figure S6. (a) Electron mobility, (b) Hole mobility of BHJ active layer and BHJ + QDs hybrid active layer devices calculated by Mott-Gurney space charge limited current (SCLC) method.

Figure S7. Contact angle and surface energy characteristics of (a) PTB7, (b) PC₇₁BM and (c) InP QDs.

Table S1. Photovoltaic performances of InP QDs + PC₇₁BM BHJ solar cells

Table S2. Photovoltaic performances of InP QDs + PC₇₁BM BHJ solar cells with respect to InP QDs ratio optimization.

Supplementary Figures

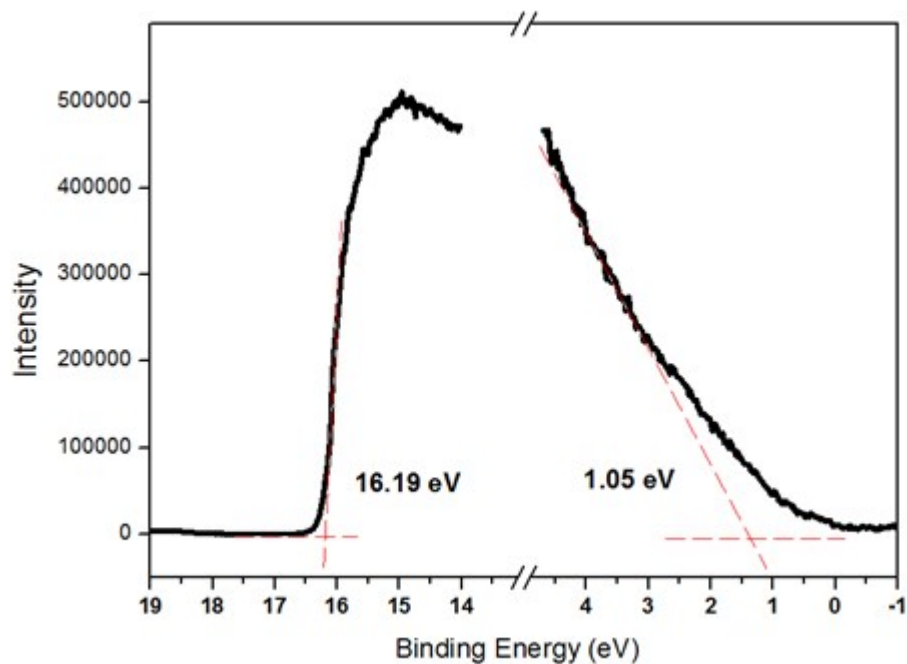


Figure S1. Properties of InP QDs. Ultraviolet photoemission spectroscopy (UPS) to determine energy levels of InP QDs.

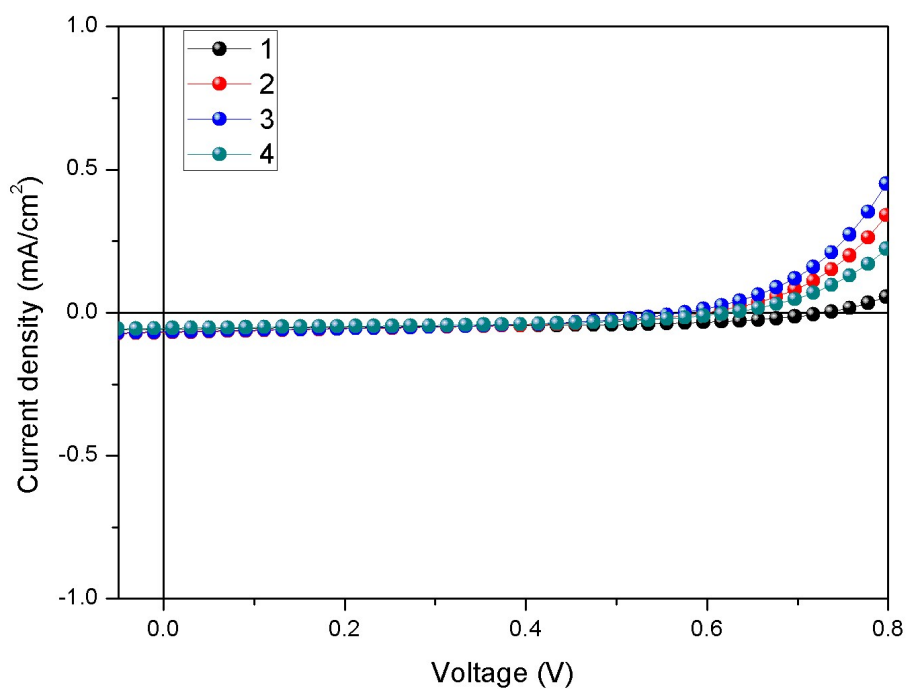


Figure S2. Performance optimization of BHJ + QDs hybrid solar cells : Current-density versus voltage (J-V) characteristics of conventional InP QDs + PC71BM BHJ solar cells under AM 1.5 G illumination with an irradiation intensity of 93 mW cm^{-2}

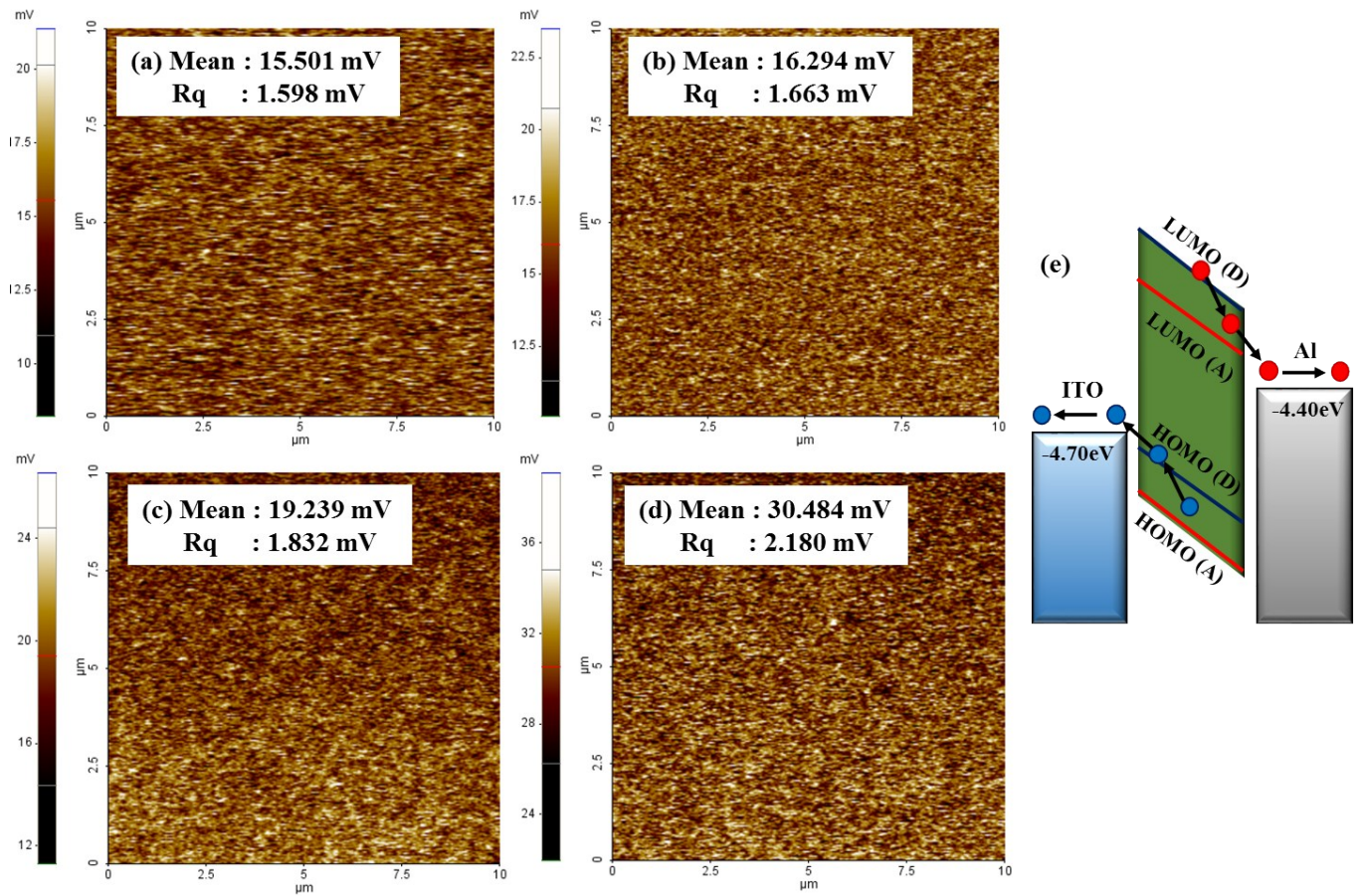


Figure S3. Electrostatic force microscopy (EFM) characteristics of (a) BJJ active layer, (b) BJJ + QDs hybrid active layer, (c) BJJ active layer with PFN interlayer and (d) BJJ + QDs hybrid active layer with PFN interlayer and (e) surface potential alignment in energy diagram in conventional structure solar cells.

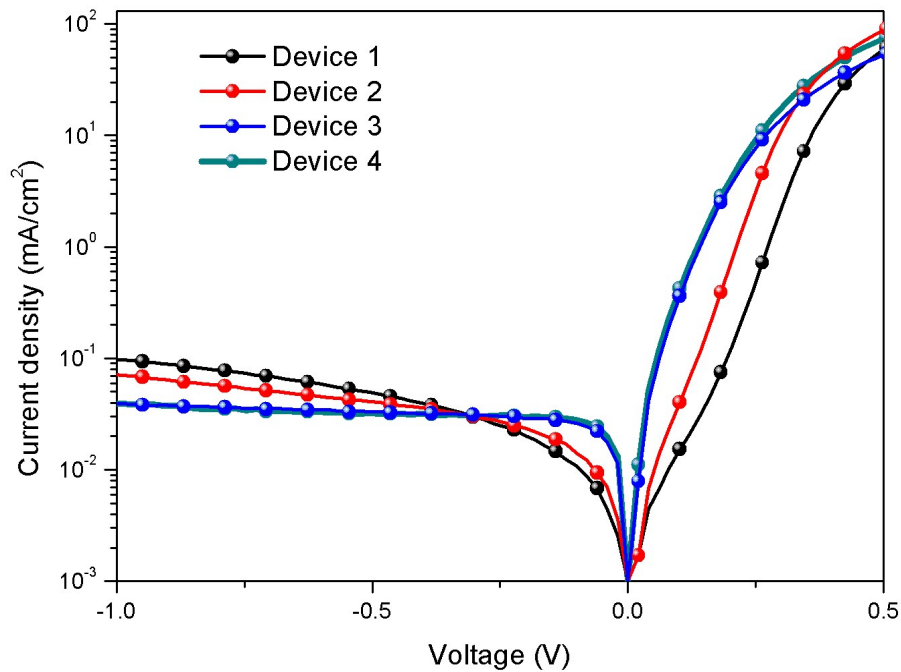


Figure S4. Dark current characteristics of BJJ + InP QDs hybrid solar cells under AM 1.5 G illumination with an irradiation

intensity of 93 mW cm^{-2}

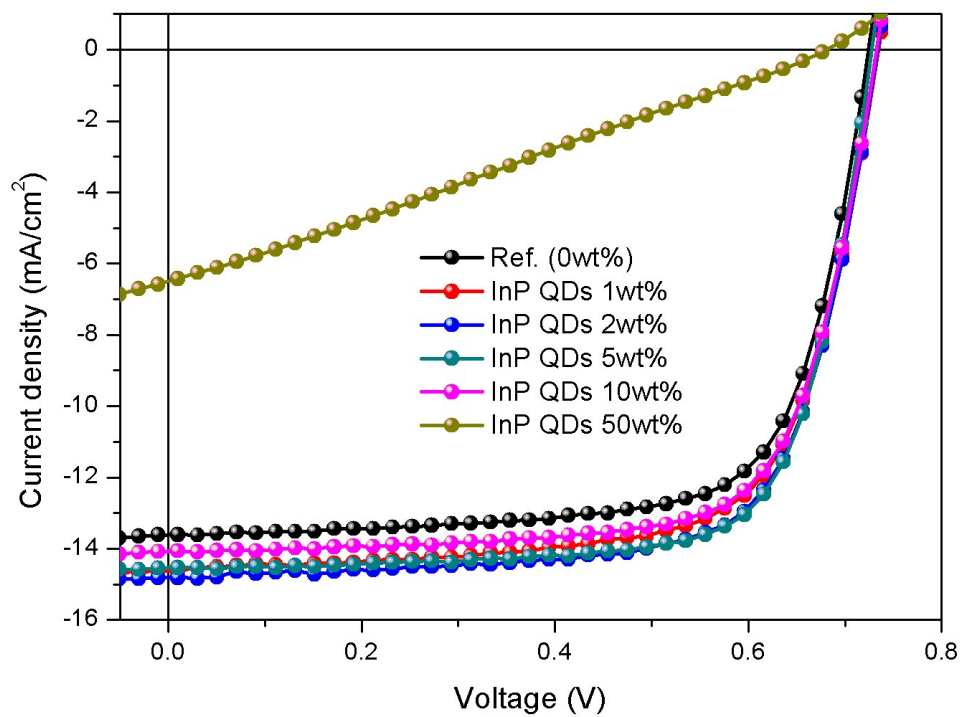


Figure S5. Ratio optimization of BHJ + QDs hybrid solar cells : Current density versus voltage (J-V) characteristics of conventional InP Qs + PC₇₁BM solar cells under AM 1.5 G illumination with an irradiation intensity of 93 mW cm^{-2}

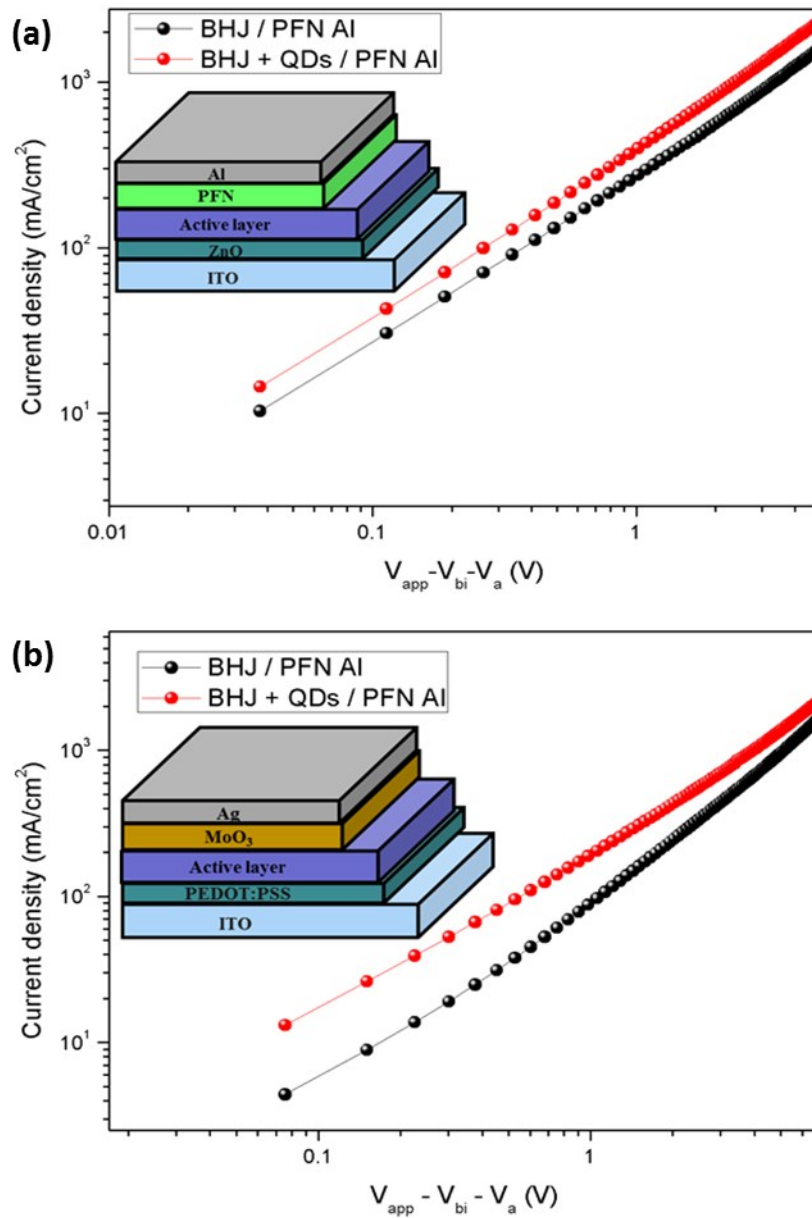


Figure S6. (a) Electron mobility, (b) Hole mobility of BHJ active layer and BHJ + QDs hybrid active layer devices calculated by Mott-Gurney space charge limited current (SCLC) method.

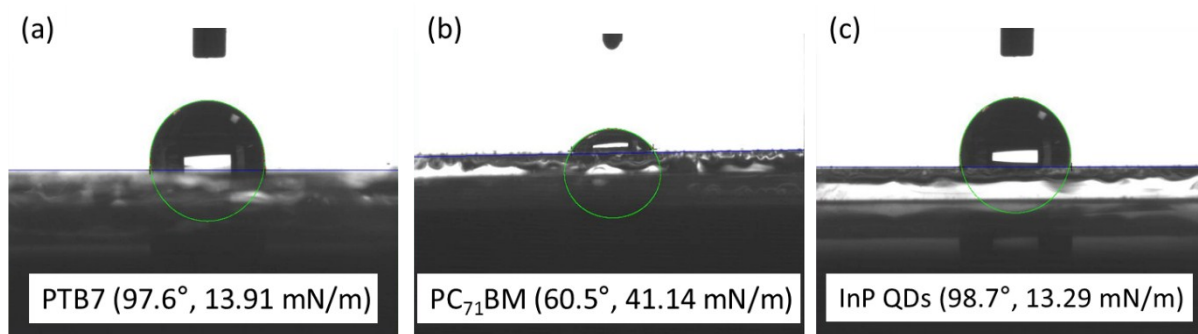


Figure S7. Contact angle and surface energy characteristics of (a) PTB7, (b) PC₇₁BM and (c) InP QDs.

Supplementary Table

Table S1. Photovoltaic performances of InP QDs + PC₇₁BM BHJ solar cells

Device structure	Jsc [mA/cm ²]	Voc [V]	FF [%]	PCE [%]
Device S1	0.039	0.696	45.4	0.013
Device S2	0.037	0.636	45.2	0.011
Device S3	0.057	0.737	49.5	0.022
Device S4	0.067	0.595	42.5	0.018

Fabricated solar cells structure : ITO/PEDOT:PSS/active layer(InP + PC₇₁BM)/Al

Table S2. Photovoltaic performances of InP QDs + PC₇₁BM BHJ solar cells with respect to InP QDs ratio optimization.

Device structure	Jsc [mA/cm ²]	Voc [V]	FF [%]	PCE [%]
BHJ (Device 4)	13.6	0.717	72.2	7.6
BHJ + 1 wt% InP QDs	14.6	0.737	69.2	7.9
BHJ + 2 wt% InP QDs	14.8	0.737	70.7	8.1
BHJ + 5 wt% InP QDs	14.5	0.737	72.6	8.4
BHJ + 10 wt% InP QDs	14.1	0.737	71.1	7.9
BHJ + 50 wt% InP QDs	6.4	0.676	26.5	1.2

Fabricated solar cells structure : ITO/PEDOT:PSS/active layer(InP + PC₇₁BM)/PFN/Al